BT152-500RT



SCR

Rev. 2 — 9 June 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated Silicon Controlled Rectifier in a SOT78 (TO-220AB) plastic package intended for use in applications requiring very high inrush current capability, high junction temperature capability and high thermal cycling performance.

1.2 Features and benefits

- High junction temperature capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Very high current surge capability

1.3 Applications

- Ignition circuits
- Motor control

- Protection circuits e.g. SMPS inrush current
- Voltage regulation

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|--------------------------------------|---|-----|-----|-----|------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 500 | V |
| V_{RRM} | repetitive peak reverse voltage | | - | - | 500 | V |
| I _{TSM} | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms | - | - | 220 | Α |
| | | half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; see Figure 4; see Figure 5 | - | - | 200 | Α |
| I _{T(AV)} | average on-state current | half sine wave; T _{mb} ≤ 122 °C; see <u>Figure 3</u> | - | - | 13 | Α |
| I _{T(RMS)} | RMS on-state current | half sine wave; see Figure 1; see Figure 2 | - | - | 20 | Α |
| Static char | acteristics | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 100 \text{ mA};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$ | - | 3 | 32 | mA |



2. Pinning information

Table 2. Pinning information

| Pin S | Symbol | Description | Simplified outline | Graphic symbol |
|-------|--------|-----------------------------------|--------------------|----------------|
| 1 K | < | cathode | | . 51 |
| 2 A | 4 | anode | mb | A H K |
| 3 G | G | gate | | G sym037 |
| mb A | A | mounting base; connected to anode | SOT78 (TO-220AB) | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|----------|--|---------|
| | Name | Description | Version |
| BT152-500RT | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |

4. Limiting values

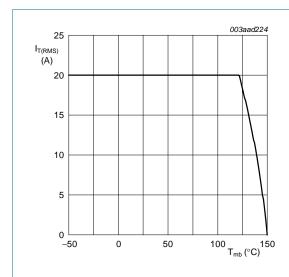
Table 4. Limiting values

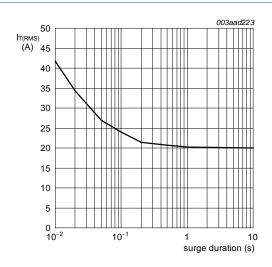
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| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|-----------------------------------|---|-----|-----|------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 500 | V |
| V _{RRM} | repetitive peak reverse voltage | | - | 500 | V |
| I _{T(AV)} | average on-state current | half sine wave; T _{mb} ≤ 122 °C; see <u>Figure 3</u> | - | 13 | Α |
| I _{T(RMS)} | RMS on-state current | half sine wave; see Figure 1; see Figure 2 | - | 20 | Α |
| I _{TSM} | non-repetitive peak on-state | half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 \text{ms}$ | - | 220 | Α |
| | current | half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$; see Figure 4; see Figure 5 | - | 200 | Α |
| l ² t | I ² t for fusing | t _p = 10 ms; sine-wave pulse | - | 200 | A ² s |
| dl _T /dt | rate of rise of on-state current | $I_T = 50 \text{ A}$; $I_G = 200 \text{ mA}$; $dI_G/dt = 200 \text{ mA/}\mu\text{s}$ | - | 200 | A/µs |
| I _{GM} | peak gate current | | - | 5 | Α |
| V_{RGM} | peak reverse gate voltage | | - | 5 | V |
| P_{GM} | peak gate power | | - | 20 | W |
| P _{G(AV)} | average gate power | over any 20 ms period | - | 1 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| T _j | junction temperature | | - | 150 | °C |

BT152-500RT

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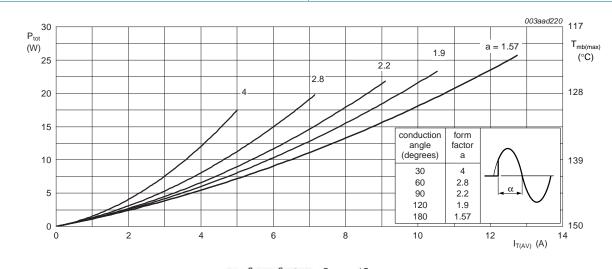




 $f = 50 \text{ Hz}; T_{mb} = 122 \text{ °C}$

Fig 1. RMS on-state current as a function of mounting base temperature; maximum values

Fig 2. RMS on-state current as a function of surge duration; maximum values



 $a = \text{form factor} = I_{T(RMS)} / I_{T(AV)}$

Fig 3. Total power dissipation as a function of average on-state current; maximum values

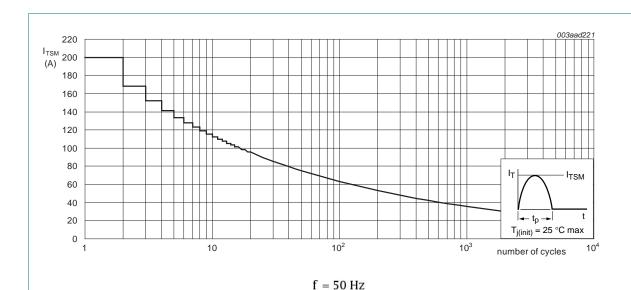


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

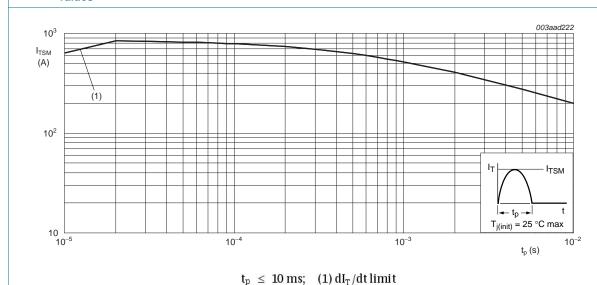
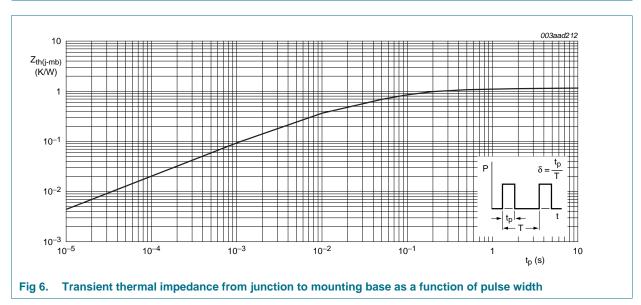


Fig 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

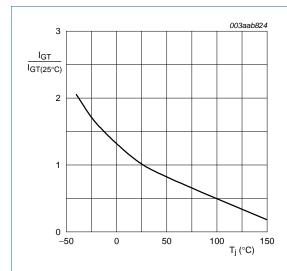
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|--------------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | see Figure 6 | - | - | 1.1 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | in free air | - | 60 | - | K/W |



6. Characteristics

Table 6. Characteristics

| Characteristics | | | | | |
|-----------------------------------|---|---|---|--|--|
| Parameter | Conditions | Min | Тур | Max | Unit |
| racteristics | | | | | |
| gate trigger current | $V_D = 12 \text{ V; } I_T = 100 \text{ mA; } T_j = 25 \text{ °C; see}$ Figure 7 | - | 3 | 32 | mA |
| latching current | $V_D = 12 \text{ V}; I_G = 100 \text{ mA}; T_j = 25 ^{\circ}\text{C};$ see Figure 8 | - | 25 | 80 | mA |
| holding current | T _j = 25 °C; see <u>Figure 9</u> | - | 15 | 60 | mA |
| on-state voltage | $I_T = 40 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{}$ | - | 1.4 | 1.75 | V |
| gate trigger voltage | $V_D = 12 \text{ V; } I_T = 100 \text{ mA; } T_j = 25 \text{ °C; see}$ Figure 11 | - | 0.6 | 1.5 | V |
| | $V_D = 500 \text{ V}; I_T = 100 \text{ mA}; T_j = 125 \text{ °C};$ see Figure 11 | 0.25 | 0.4 | - | V |
| off-state current | V _D = 500 V; T _j = 125 °C | - | 0.2 | 1 | mΑ |
| reverse current | T _j = 125 °C; V _R 500 V | - | 0.2 | 1 | mA |
| characteristics | | | | | |
| rate of rise of off-state voltage | V_{DM} = 335 V; T_j = 125 °C; exponential waveform; gate open circuit; see Figure 12 | 200 | 300 | - | V/µs |
| gate-controlled turn-on time | $I_{TM} = 40 \text{ A}; V_D = 500 \text{ V}; I_G = 100 \text{ mA};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$ | - | 2 | - | μs |
| commutated turn-off time | $V_{DM} = 335 \text{ V; } T_j = 125 \text{ °C; } I_{TM} = 20 \text{ A;}$ $V_R = 25 \text{ V; } (dI_T/dt)_M = 30 \text{ A/µs;}$ $dV_D/dt = 50 \text{ V/µs; } R_{GK} = 100 \Omega$ | - | 70 | - | μs |
| | Parameter aracteristics gate trigger current latching current holding current on-state voltage gate trigger voltage off-state current reverse current characteristics rate of rise of off-state voltage gate-controlled turn-on time | Parameter Conditions practeristics gate trigger current $V_D = 12 \text{ V}; I_T = 100 \text{ mA}; T_j = 25 \text{ °C}; \text{ see} \frac{\text{Figure 7}}{\text{Figure 7}}$ latching current $V_D = 12 \text{ V}; I_G = 100 \text{ mA}; T_j = 25 \text{ °C}; \text{ see} \frac{\text{Figure 8}}{\text{Figure 8}}$ holding current $T_j = 25 \text{ °C}; \text{ see Figure 9}$ on-state voltage $I_T = 40 \text{ A}; T_j = 25 \text{ °C}; \text{ see} \frac{\text{Figure 10}}{\text{Figure 11}}$ $V_D = 12 \text{ V}; I_T = 100 \text{ mA}; T_j = 25 \text{ °C}; \text{ see} \frac{\text{Figure 11}}{\text{Figure 11}}$ $V_D = 500 \text{ V}; I_T = 100 \text{ mA}; T_j = 125 \text{ °C}; \text{ see} \frac{\text{Figure 11}}{\text{Figure 11}}$ off-state current $V_D = 500 \text{ V}; T_j = 125 \text{ °C}; \text{ exponential}$ reverse current $T_j = 125 \text{ °C}; V_R = 500 \text{ V}; \text{ Voltage}$ rate of rise of off-state waveform; gate open circuit; see Figure 12 gate-controlled turn-on time $V_D = 335 \text{ V}; T_j = 125 \text{ °C}; I_{TM} = 20 \text{ A}; V_R = 25 \text{ V}; (dI_T/dt)_M = 30 \text{ A}/\mu\text{s};$ | $ \begin{array}{c} \textbf{Parameter} & \textbf{Conditions} & \textbf{Min} \\ \textbf{aracteristics} \\ \\ \textbf{gate trigger current} & V_D = 12 \ V; \ I_T = 100 \ \text{mA}; \ T_j = 25 \ ^{\circ}\text{C}; \ \text{see} \\ \hline \textbf{Figure 7} \\ \\ \textbf{latching current} & V_D = 12 \ V; \ I_G = 100 \ \text{mA}; \ T_j = 25 \ ^{\circ}\text{C}; \ \text{see} \\ \hline \textbf{Figure 8} \\ \\ \textbf{holding current} & T_j = 25 \ ^{\circ}\text{C}; \ \text{see} \ \textbf{Figure 9} \\ \textbf{on-state voltage} & I_T = 40 \ \text{A}; \ T_j = 25 \ ^{\circ}\text{C}; \ \text{see} \ \textbf{Figure 10} \\ \hline \textbf{gate trigger voltage} & V_D = 12 \ \text{V}; \ I_T = 100 \ \text{mA}; \ T_j = 25 \ ^{\circ}\text{C}; \ \text{see} \\ \hline \textbf{Figure 11} \\ \hline \textbf{V}_D = 500 \ \text{V}; \ I_T = 100 \ \text{mA}; \ T_j = 125 \ ^{\circ}\text{C}; \ \text{see} \\ \hline \textbf{Figure 11} \\ \hline \textbf{off-state current} & V_D = 500 \ \text{V}; \ T_j = 125 \ ^{\circ}\text{C}; \ \textbf{exponential} \\ \hline \textbf{voltage} & \text{waveform}; \ \text{gate open circuit}; \\ \hline \textbf{see} \ \textbf{Figure 12} \\ \hline \textbf{gate-controlled turn-on time} & I_{TM} = 40 \ \text{A}; \ V_D = 500 \ \text{V}; \ I_G = 100 \ \text{mA}; \ - \\ \hline \textbf{d}_{I_G}/\text{dt} = 5 \ \text{A}/\mu\text{s} \\ \hline \textbf{commutated turn-off time} & V_{DM} = 335 \ \text{V}; \ T_j = 125 \ ^{\circ}\text{C}; \ I_{TM} = 20 \ \text{A}; \ - \\ \hline \textbf{V}_R = 25 \ \text{V}; \ (\text{dI}_T/\text{dt})_M = 30 \ \text{A}/\mu\text{s}; \\ \hline \end{array}$ | $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$ | $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$ |





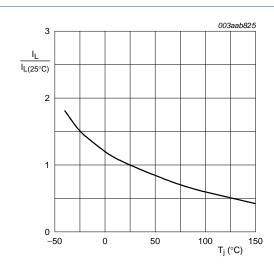
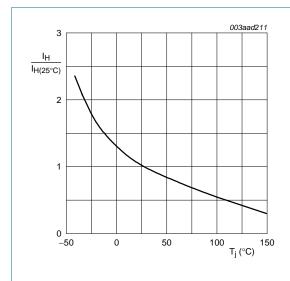


Fig 8. Normalized latching current as a function of junction temperature

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10 003aad219
20 (1) (2) (3) 10
0 1 2 V_T (V)

Vo = 1.06 V; Rs = 0.03 Ω

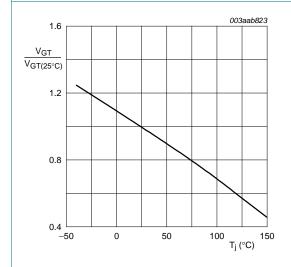
(1) Tj = 150 °C; typical values

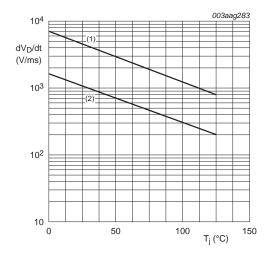
(2) Tj = 150 °C; maximum values

(3) Tj = 25 °C; maximum values

Fig 9. Normalized holding current as a function of junction temperature







(1) $R_{GK} = 100 \Omega$

(2) Gate open circuit

Fig 11. Normalized gate trigger voltage as a function of junction temperature

Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

7. Package outline

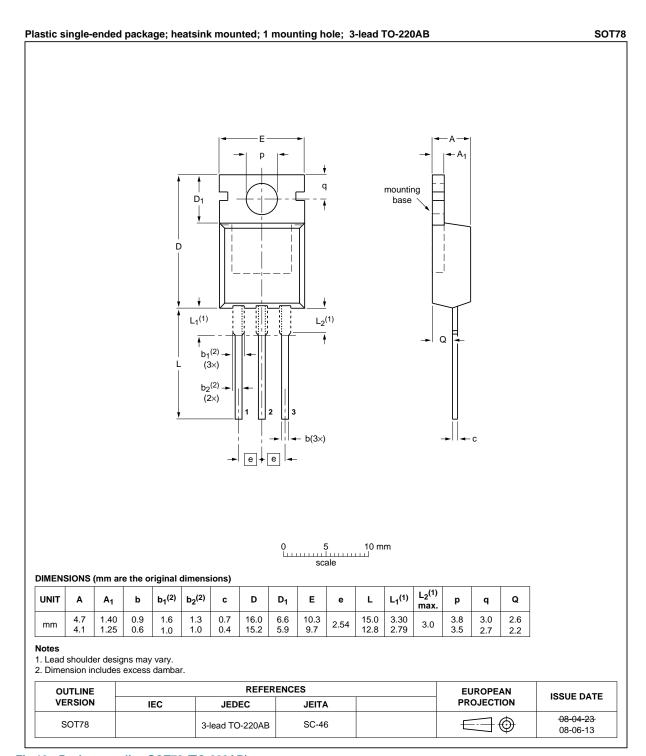


Fig 13. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-----------------|------------------------------------|--------------------|---------------|-----------------|
| BT152-500RT v.2 | 20110609 | Product data sheet | - | BT152-500RT v.1 |
| Modifications: | Various change | es to content. | | |
| BT152-500RT v.1 | 20090512 | Product data sheet | - | - |

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